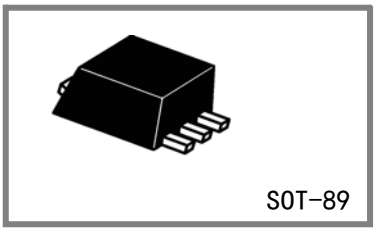
KTC4373Y

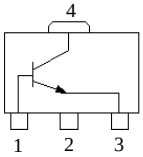
NPN-General use transistor

1W 1A 80V



Applications： Can be used for switching and amplifying in various electrical and electronic equipments.

Circuit：



MARKING

CY

Max ratings

Parameters	Symbol	Rating	Unit
Collector–emitter voltage（I_B=0）	V_{CEO}	80	V
Collector–base voltage（I_E=0）	V_{CBO}	100	V
Emitter – base voltage（I_C=0）	V_{EBO}	5	V
Collector current	I_C	1	A
Total power dissipation（T_A=25℃）*	P_{tot}	1	W
Max junction temperature	T_{jm}	150	℃
Storage temperature	T_{stg}	-55～150	℃
* mounted on printed circuit board.			

Characteristics（Unless otherwise specified，T_A=25℃）

Parameters	symbol	Test condition	min	typ	max	unit
Collector–emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA，I_B=0	80	—	—	V
Collector–base breakdown voltage	$V_{(BR)CBO}$	I_C=100μA，I_E=0	100	—	—	V
Emitter– base breakdown voltage	$V_{(BR)EBO}$	I_E=100μA，I_C=0	5	—	—	V
Forward current transfer ratio[1)]	h_{FE}	V_{CE}=2V；I_C=150mA	120	—	240	—
Collector–base cutoff current	I_{CBO}	V_{CB}=30V，I_E=0	—	—	100	nA
Collector–emitter saturation voltage[1)]	$V_{CE（sat）}$	I_C=500mA，I_B=50mA	—	—	0.5	V
Transition frequency	f_T	I_C=10mA，V_{CE}=5V，f=100MHz	—	130	—	MHz
[1)] pulse method：t_w:300μs，duty ratio≤2%.						

Typical curve

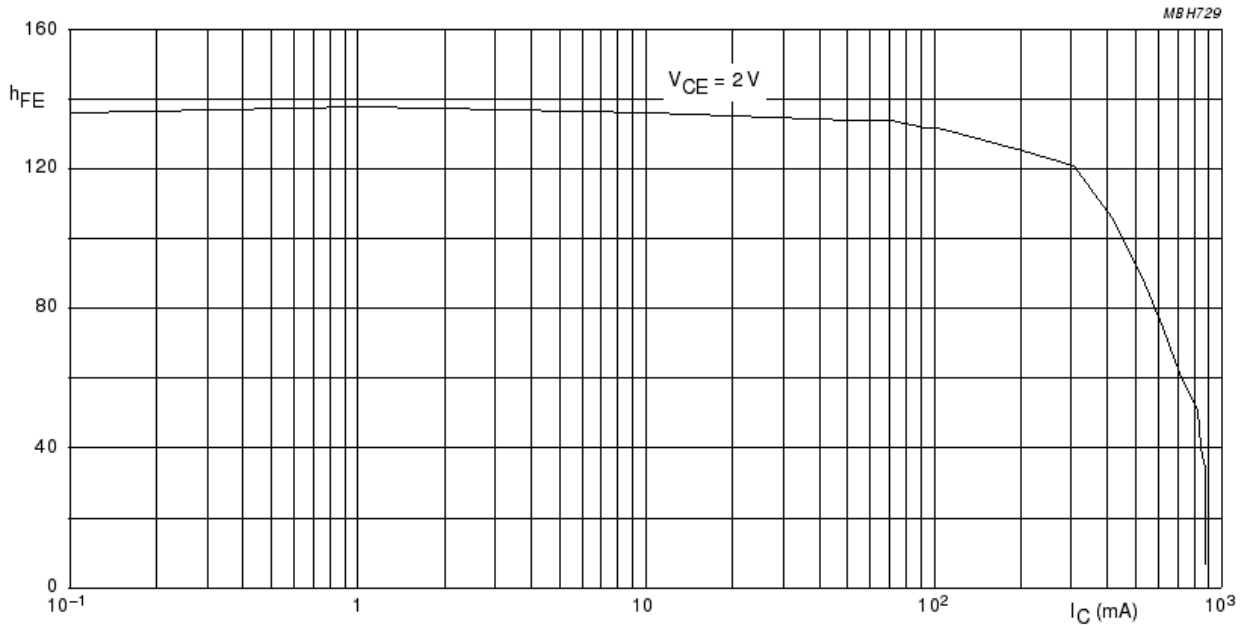
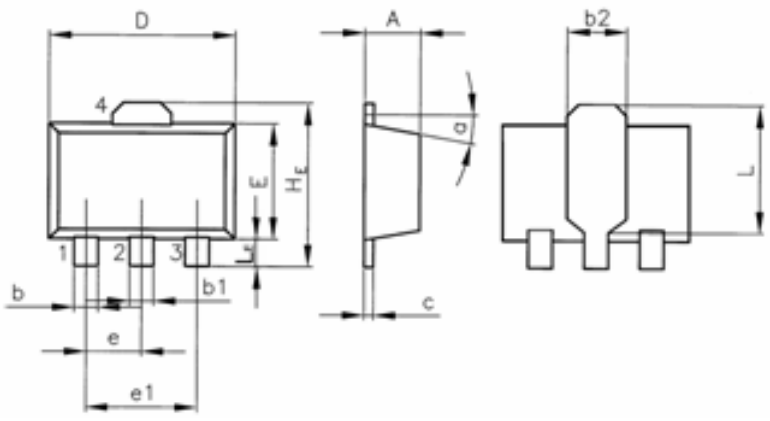


Fig.1 DC current gain; typical values.

Outline dimensions



unit：mm

尺寸 符号	SOT-89		
	min	type	max
A	1.4		1.6
b	0.35		0.55
b1	0.4		0.65
b2		1.6	
c	0.35		0.45
D	4.4		4.6
E	2.35		2.55
e		1.5	
e1		3	
HE		4.15	
L		2.7	
LE		1.0	
α		5o	